SiBP12R75/1R3-9D3

Features

High precision

MEMS process

High performance, shielded, Micro-Cavity structure

Silicon base, 50 Ω CPW output

Au bonding for MCM application

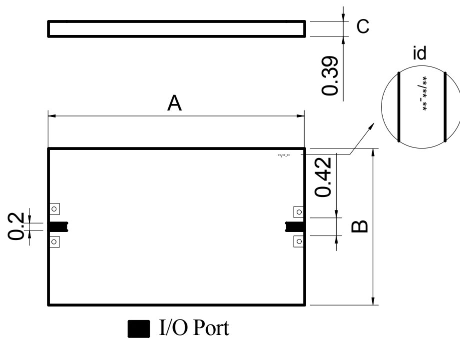
Environmental Parameter

Operating Temperature	-55℃~+85℃
Storage Temperature	-55℃~+125℃
Highest Input Power	35dBm

Electrical Parameter(TA=+25℃)

Item	Min.	Typical	Max.	Unit
Central Frequency(f_0)	-	12.75	-	GHz
Passband Frequency Range	12.1	-	13.4	GHz
Passband Ripple	-	-	1	dB
Central Insertion Loss	-	3	-	dB
Return Loss	-	15	-	dB
Out Band Attenuation	⩾35@10.9GHz			dB
	⩾35@14.6GHz			dB

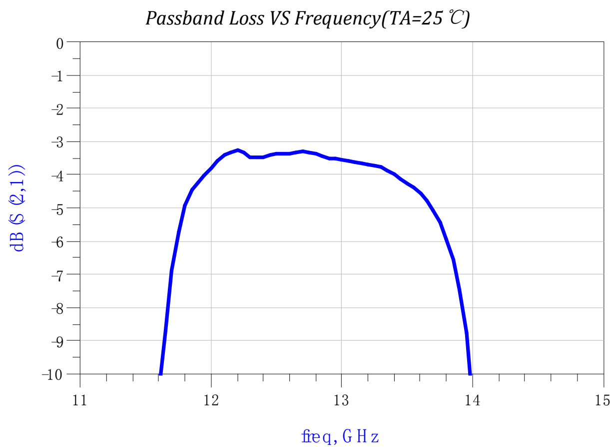
Overall Dimension



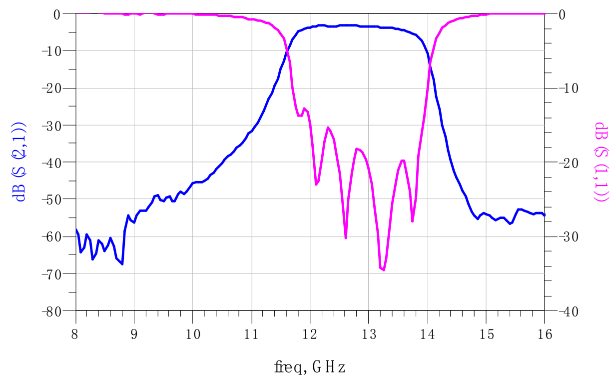
Dimension Symbols	Value(mm)		
	Min.	Nominal	Max.
A	7.9	-	8
B	2.7	-	2.8

Typical Testing Curve

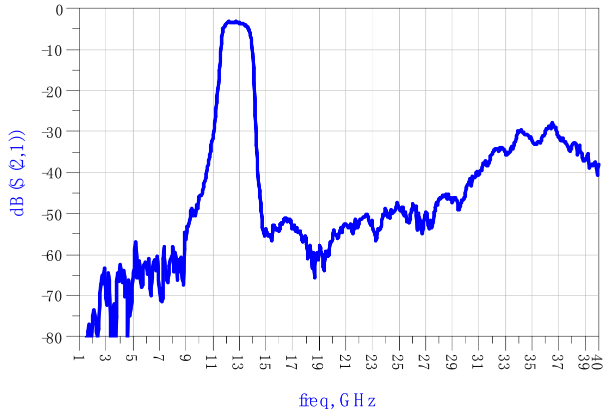
Passband Loss VS Frequency(TA=25 ℃)



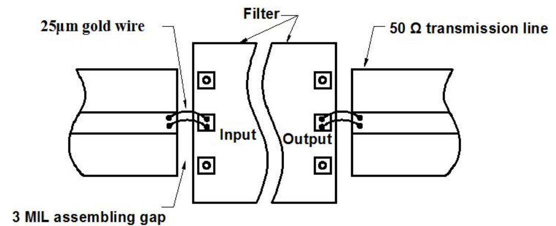
Outband Attenuation & Return Loss VS Frequency(TA=25 ℃)



Far-end Attenuation VS Frequency TA=25 ℃)



Assembly Diagram



Note:

1. Au bonding ribbon width=150um, thinkness=12.5um, as short as possible.
2. Recommended space between chip and cover:1-3mm
3. Low temperature assembly technology:180℃ Max
4. The center RF stripline of CPW can be connected directly to the microstrip line of customer.
5. Top surface bonded to Ground is helpful for high l stopband rejection.
6. Underlayed metal: Cova (recommended).